Features

- Split Gate Trench MOSFET technology
- Excellent Package for Heat Dissipation
- High Density Cell Desihn for Low $R_{DS(on)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

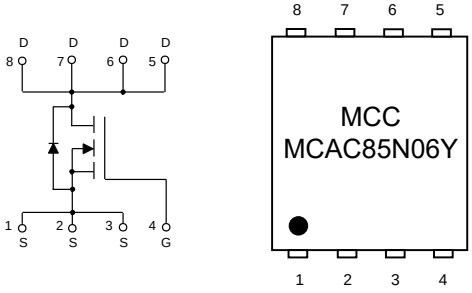
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 55°C/W Junction to Ambient(Note 2)
- Thermal Resistance: 1.2°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Volltage		V_{GS}	±20	V
Drain Current		I_D	130	A
Continuous Drain Current(Note 3)	T_C=25°C	I_D	85	A
	T_C=100°C		54	A
Pulsed Drain Current (Note 4)		I_{DM}	390	A
Single Pulse Avalanche Energy (Note 5)		E_{AS}	270	mJ
Total Power Dissipation (Note 6)		P_D	105	W

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The Value of $R_{\theta JA}$ is Measured with the Device Mounted on 1 in^2 FR-4 Board with 2oz. Copper, in a Still Air Environment with T_A=25°C.
3. The Maximum Current Rating is Package Limited.
4. Pulse Width Limited by Max. Junction Temperature.
5. V_{DD}=50 V, R_G=25 Ω, L=0.5mH, starting T_J=25°C.
6. PD is Based on Max. Junction Temperature, Using Junction-Case Thermal Resistance.

Internal Structure and Marking Code



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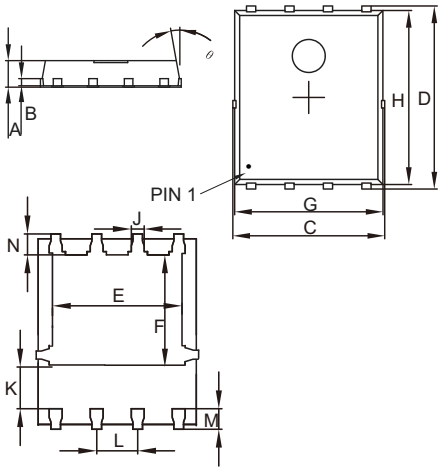


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A		2.5	3	mΩ
		V_{GS}=4.5V, I_D=10A		3.5	4.5	
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A			1.2	V
Continuous Body Diode Current	I_S				85	A
Dynamic Characteristics(Note 7)						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHz		3350		pF
Output Capacitance	C_{oss}			1666		
Reverse Transfer Capacitance	C_{rss}			77.7		
Total Gate Charge	Q_g	V_{DS}=30V,V_{GS}=10V,I_D=25A		66.1		nC
Gate-Source Charge	Q_{gs}			10.7		
Gate-Drain Charge	Q_{gd}			10.9		
Reverse Recovery Chrage	Q_{rr}	I_S=25A, di/dt=100A/μs		73		
Reverse Recovery Time	t_{rr}			68		ns
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=30V,I_D=25A R_{GEN}=2Ω		22.5		
Turn-On Rise Time	t_r			6.7		
Turn-Off Delay Time	$t_{d(off)}$			80.3		
Turn-Off Fall Time	t_f			26.9		

Note 7.Guaranteed by Design, Not Subject to Production Testing.

Curve Characteristics

Fig. 1 - Typical Output Characteristics

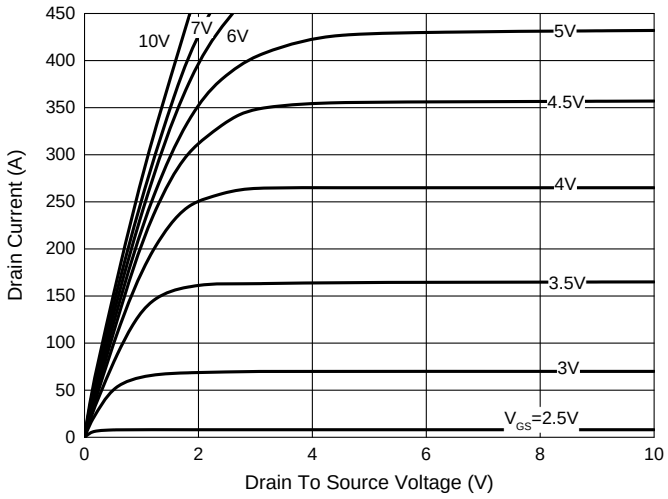


Fig. 2 - Drain-Source Breakdown Voltage

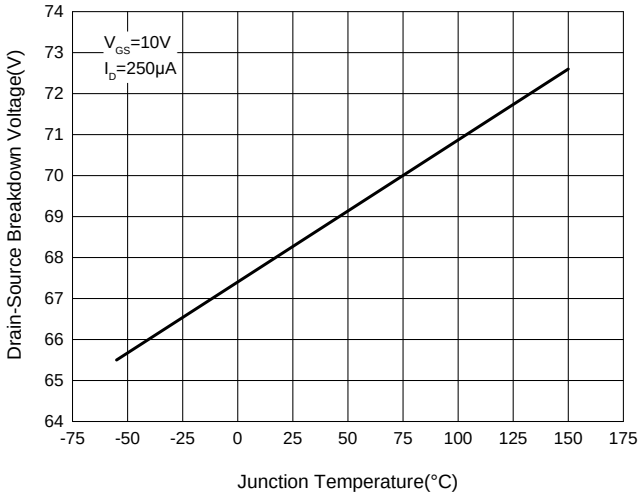


Fig. 3 - Capacitance Characteristics

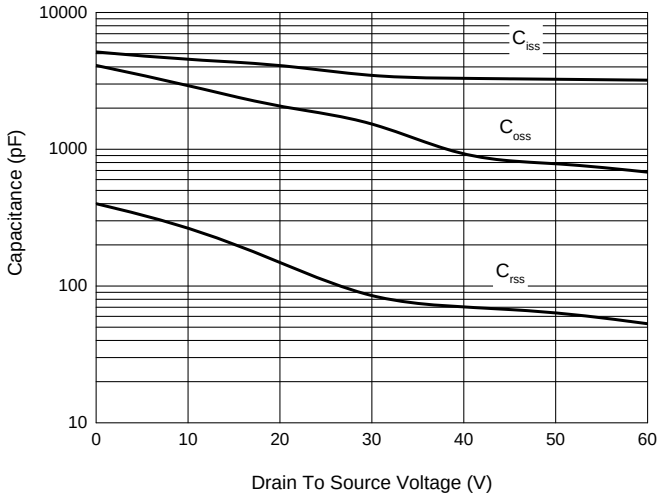


Fig. 4 - Gate Charge Characteristics

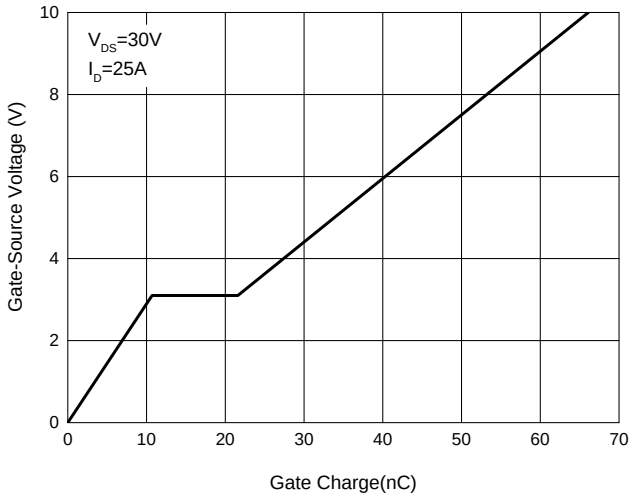


Fig. 5 - On Resistance Characteristics

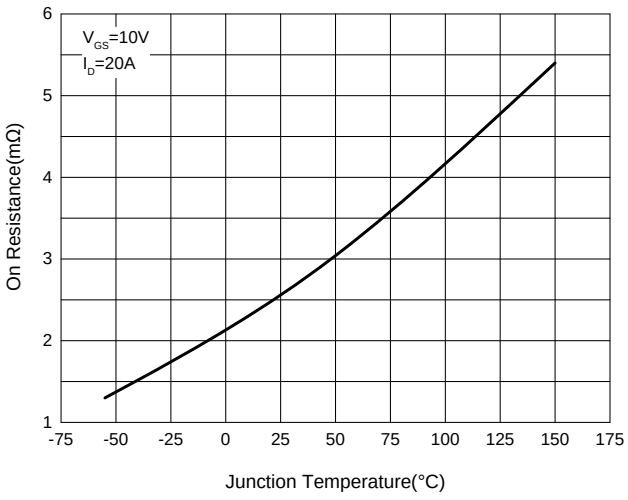
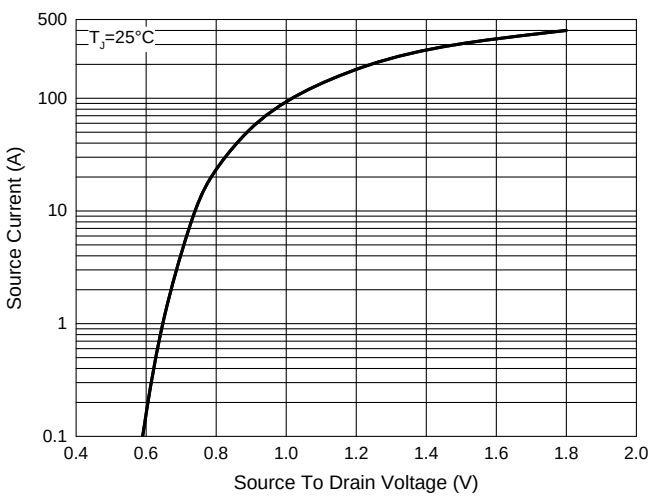


Fig. 6 - I_S—V_{SD}



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel